

# Euijun Cha

## List of Publications by Year in descending order

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13  
papers

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citing authors

#	ARTICLE	IF	CITATIONS
1	Multi-layered NiOy/NbOx/NiOy fast drift-free threshold switch with high Ion/Ioff ratio for selector application. Scientific Reports, 2017, 7, 4068.	1.6	59
2	Dynamics of electroforming and electrically driven insulator-metal transition in NbOx selector. Applied Physics Letters, 2016, 108, .	1.5	42
3	Comprehensive scaling study of NbO2 insulator-metal-transition selector for cross point array application. Applied Physics Letters, 2016, 108, .	1.5	84
4	Control of Cu Conductive Filament in Complementary Atom Switch for Cross-Point Selector Device Application. IEEE Electron Device Letters, 2014, 35, 60-62.	2.2	31
5	Optimized Lightning-Rod Effect to Overcome Trade-Off Between Switching Uniformity and On/Off Ratio in ReRAM. IEEE Electron Device Letters, 2014, 35, 214-216.	2.2	6
6	BEOL compatible (300Å;C) TiN/TiO <sub>x</sub> /Ta/TiN 3D nanoscale (<math>10\text{nm}</math>) IMT selector. , 2013, , .		8
7	Vertically Stacked ReRAM Composed of a Bidirectional Selector and CB-RAM for Cross-Point Array Applications. IEEE Electron Device Letters, 2013, 34, 1512-1514.	2.2	25
8	Defect Engineering Using Bilayer Structure in Filament-Type RRAM. IEEE Electron Device Letters, 2013, 34, 1250-1252.	2.2	10
9	Multilayer-oxide-based bidirectional cell selector device for cross-point resistive memory applications. Applied Physics Letters, 2013, 103, .	1.5	13
10	Improved switching uniformity in resistive random access memory containing metal-doped electrolyte due to thermally agglomerated metallic filaments. Applied Physics Letters, 2012, 100, .	1.5	27
11	High Current Density and Nonlinearity Combination of Selection Device Based on TaO <sub>x</sub> /TiO <sub>2</sub> /TaO <sub>x</sub> Structure for One Selector "One Resistor Arrays. ACS Nano, 2012, 6, 8166-8172.	7.3	138
12	Highly uniform and reliable resistance switching properties in bilayer WO <sub>x</sub> /NbO <sub>x</sub> RRAM devices. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1179-1183.	0.8	37
13	Effect of interfacial oxide layer on the switching uniformity of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> -based resistive change memory devices. Applied Physics Letters, 2011, 99, 162109.	1.5	15